

Based on Form PTO-1449 (3/90)				ATTY. DOCKET NO. 790001-2002		SERIAL NO. Not Yet Known	
LIST OF REFERENCES CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Yoshitaka Tsunashima et al.			
				FILING DATE March 9, 2001		GROUP Not Yet Known	

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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
<i>QMB</i>	AA	5,963,810	Gardner et al.				
<i>QMB</i>	AB	5,834,353	Wu				
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						

FOREIGN PATENT DOCUMENTS								
DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION			
					YES	NO		
<i>QMB</i>	AI	11-135774	5/21/99	Japan		X		
<i>QMB</i>	AJ	3-74878	5/29/91	Japan		X		
	AK							

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)		
<i>QMB</i>	AL	Copel et al., <i>Structure and Stability of Ultrathin Zirconium Oxide Layers on Si(001)</i> , <u>Applied Physics Letters</u> , Vol. 76, No. 4 (1/24/00), pp. 436-438
<i>QMB</i>	AM	Guo et al., <i>High Quality Ultra-thin (1.5 nm) TiO₂Si₃N₄ Gate Dielectric for Deep Sub-micron CMOS Technology</i> , International Electron Device Meeting 1999, <u>Technical Digest</u> , Session 6: Process Technology-High K Gate Dielectrics (12/8/99)
<i>QMB</i>	AN	Lee et al., <i>Ultrathin Hafnium Oxide with Low Leakage and Excellent Reliability for Alternative Gate Dielectric Application</i> , International Electron Device Meeting 1999, <u>Technical Digest</u> , Session 6: Process Technology-High K Gate Dielectrics (12/8/99)
<i>QMB</i>	AO	Luan et al., <i>High Quality Ta₂O₅ Gate Dielectrics with T_{ox,eq} < 10Å</i> , International Electron Device Meeting 1999, <u>Technical Digest</u> , Session 6: Process Technology-High K Gate Dielectrics (12/8/99)
<i>QMB</i>	AP	Ma et al., <i>Zirconium Oxide Based Gate Dielectrics with Equivalent Oxide Thickness of Less Than 1.0 nm and Performance of Submicron MOSFET using a Nitride Gate Replacement Process</i> , International Electron Device Meeting 1999, <u>Technical Digest</u> , Session 6: Process Technology-High K Gate Dielectrics (12/8/99)
<i>QMB</i>	AQ	Qi et al., <i>MOSCAP and MOSFET Characteristics Using ZrO₂ Gate Dielectric Deposited Directly on Si</i> , International Electron Device Meeting 1999, <u>Technical Digest</u> , Session 6: Process Technology-High K Gate Dielectrics (12/8/99)
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EXAMINER <i>Quafer M. Bole</i>	DATE CONSIDERED 11-13-02
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* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.